

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of) Art Unit: Unassigned
Hideomi SUZAWA et al.) Examiner: Unassigned
Serial No. 10/086,628)
Filed: March 4, 2002)
For: SEMICONDUCTOR DEVICE AND)
MANUFACTURING METHOD)
THEREOF)

CERTIFICATE OF MAILING

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Washington, D.C. 20231, on 2/7/02

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

Sir:

Please preliminarily amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 7 and 11-12 as follows:

7. (Amended) A semiconductor device according to claims 1 to 5 wherein a side face of one of the source region and the drain is aligned with one of the source wiring and the electrode.

11. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 or 9 wherein in the eighth step, a part of the first amorphous semiconductor film and the conductive film and the second amorphous semiconductor film are etched with a chlorine type gas.


12. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 or 9 wherein the chlorine type gas is selected from Cl_2 and BCl_3 , HCl and SiCl_4 or a gas containing a plurality of gases from these gases.

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REMARKS

Applicants have amended claims 7 and 11-12 to correct the dependency.
Examination on the merits is respectfully requested.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claims 7 and 11-12 as follows:

7. (Amended) A semiconductor device according to claims 1 to [6] 5 wherein a side face of one of the source region and the drain is aligned with one of the source wiring and the electrode.

11. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 [to 10] or 9 wherein in the eighth step, a part of the first amorphous semiconductor film and the conductive film and the second amorphous semiconductor film are etched with a chlorine type gas.

12. (Amended) A method of manufacturing a semiconductor device according to any one of claims 8 [to 11] or 9 wherein the chlorine type gas is selected from Cl_2 and BCl_3 , HCl and SiCl_4 or a gas containing a plurality of gases from these gases.

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